

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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PATENT • TRADEMARK

Application Number	10/826,564
Filing Date	April 16, 2004
First Named Inventor	Engbrecht et al.
Group Art Unit	2811
Examiner Name	To be assigned
Attorney Docket Number	5347-219

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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
TH	6.	Fayolle et al.; "Integration of Cu/SiOC in Dual Damascene interconnect for 0.1µm technology using a new SiC material as dielectric barrier" 2002 <i>IEEE International Interconnect Technology Conference</i> , Burlingame, CA 39-41 (2002).	
	7.	Gelatos et al.; "The Properties of a Plasma Deposited Candidate Insulator for Future Multilevel Interconnects Technology" <i>Mat. Res. Soc. Symp.</i> 250 347-354 (1992).	
	8.	Levy et al. "Evaluation of LPCVD Boron Nitride as a Low Dielectric Constant Material" <i>Mat. Res. Soc. Symp.</i> 427 469-478 (1996).	
	9.	Martin et al.; "Integration of SiCN as a Low κ Etch Stop and Cu Passivation in a High Performance Cu/Low κ Interconnect" 2002 <i>IEEE International Interconnect Technology Conference</i> , Burlingame, CA 4244 (2002).	
	10.	Nguyen et al.; "Plasma-Assisted Chemical Vapor Deposition and Characterization of Boron Nitride Films" <i>J. Electrochem. Soc.</i> , 141:6 1633-1638 (1994).	
TH	11.	Sugino et al.; "Dielectric constant of boron carbon nitride films synthesized by plasma-assisted chemical-vapor deposition" <i>Applied Physics Letters</i> 80:4 649-651 (2002).	

$$\text{Te-Te-HO}$$

Feb. 2006

Examiner Signature

Date Considered